

INK0210AC1

High Speed Switching
Silicon N-channel MOSFET

DESCRIPTION

INK0210AC1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

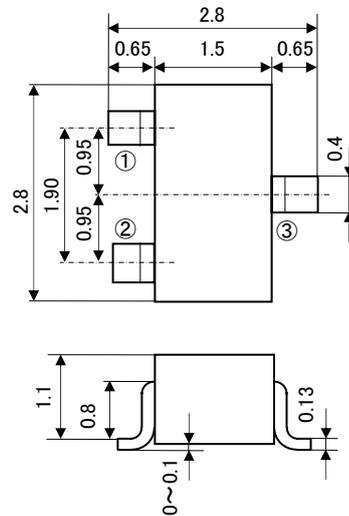
- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current $I_D=1A$
- Drive voltage 4V
- Low on Resistance. $R_{DS(on)}=0.3\Omega$ (TYP).
- High speed switching.
- Small package for easy mounting.

APPLICATION

Switching

OUTLINE DRAWING

UNIT:mm



JEITA: SC-59

JEDEC: Similar to TO-236

TERMINAL CONNECTER

①: GATE

②: SOURCE

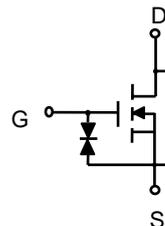
③: DRAIN

MAXIMUM RATINGS (Ta=25°C)

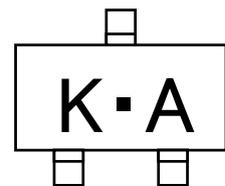
Symbol	Parameter	Rating	Unit
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current(DC)	1	A
I _{DP}	Drain current(Pulse) ※1	4	A
P _D	Total Power Dissipation	200	mW
T _{ch}	Channel Temperature	+150	°C
T _{stg}	Storage temperature	-55~+150	°C

※1: Pw ≤ 10 μs, Duty cycle ≤ 1%

EQUIVALENT CIRCUIT



MARKING



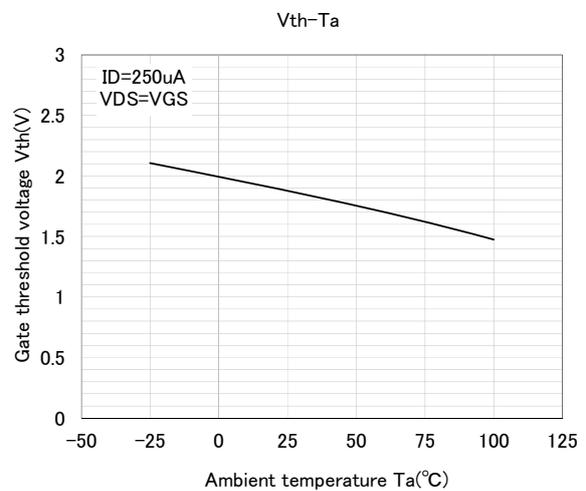
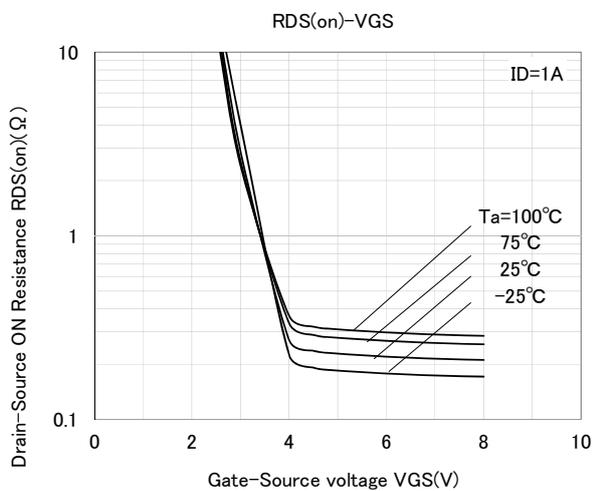
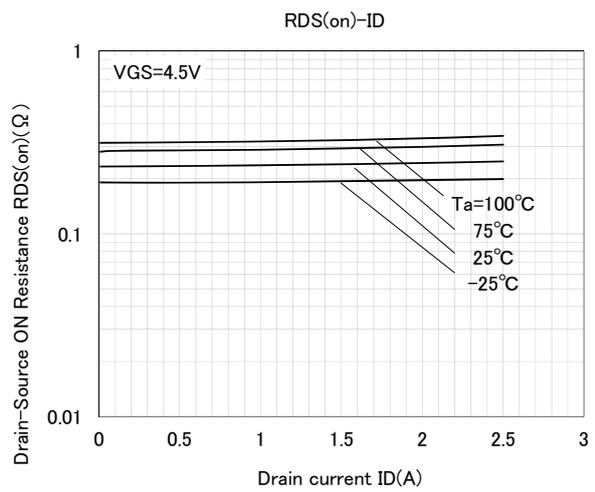
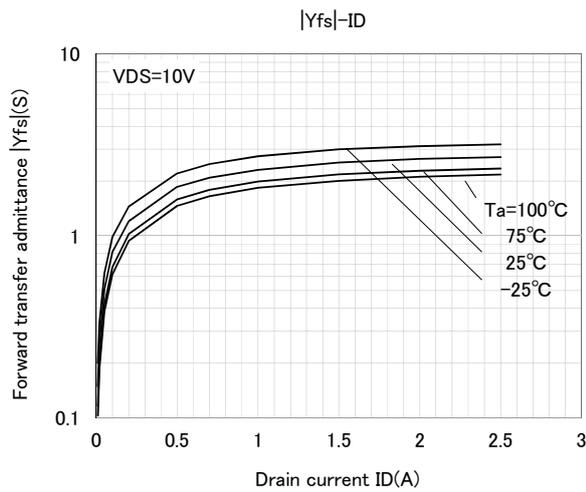
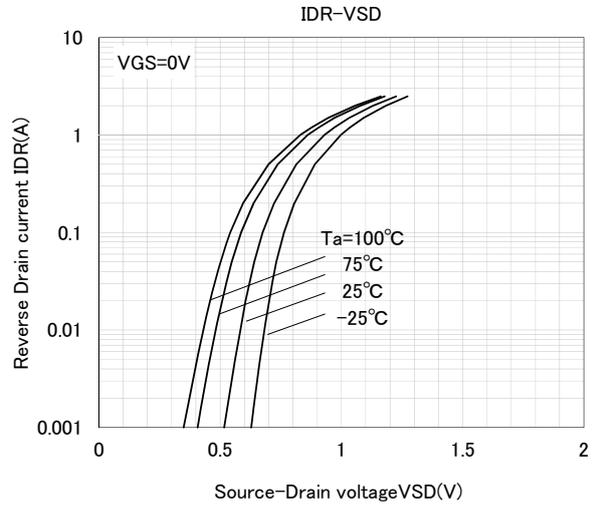
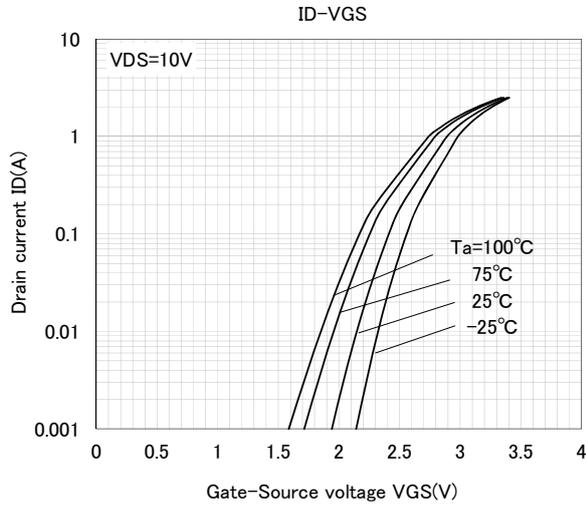
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V(BR)DSS	I _D =100 μA, V _{GS} =0V	60	-	-	V
Gate-Source Leak current	I _{GS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate Threshold Voltage	V _{th}	I _D =250 μA, V _{DS} =V _{GS}	1.0	-	2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =1A	-	2.0	-	S
Static Drain-Source On-State Resistance	R _{DS(ON)}	I _D =0.5A, V _{GS} =5.0V	-	0.30	-	Ω
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	220	-	pF
Output Capacitance	C _{oss}		-	28	-	pF
Switching Time	t _{on}	V _{DD} =30V, I _D =1A	-	16	-	ns
	t _{off}	V _{GS} =0~5V	-	25	-	ns

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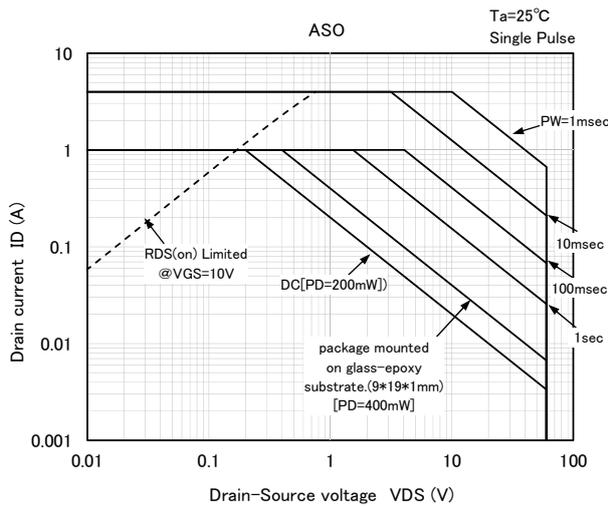
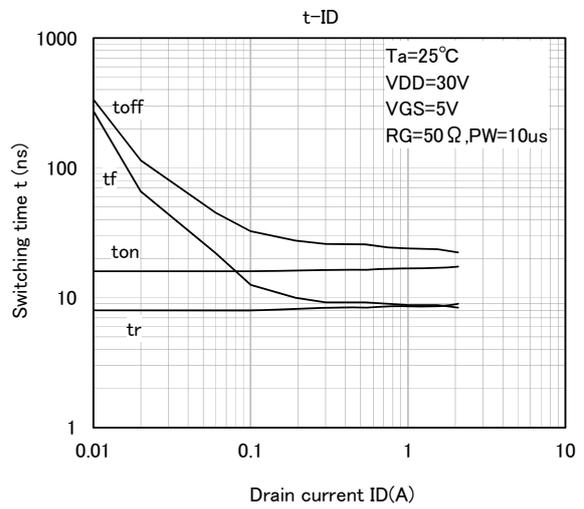
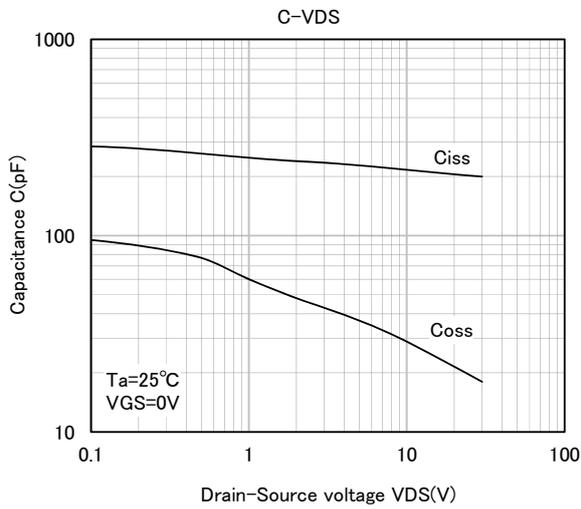
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TYPICAL CHARACTERISTICS

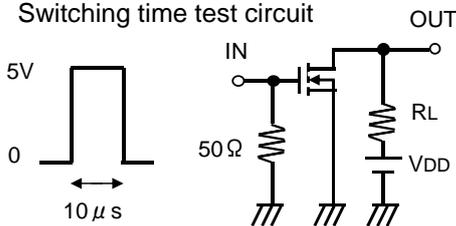


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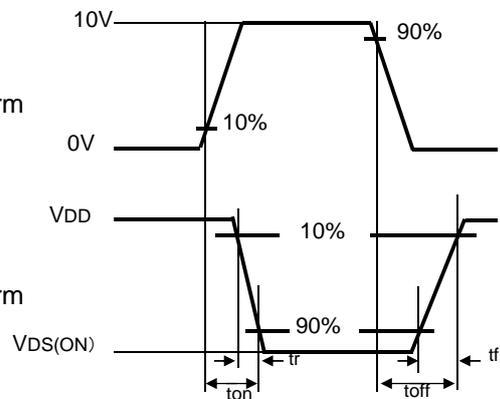
Switching time test circuit



$V_{DD}=30\text{V}$
Duty $\leq 1\%$
Input: t_r , $t_f < 10\text{ns}$
Common source
 $T_a=25^\circ\text{C}$

Input
Waveform

Output
Waveform





Keep safety first in your circuit designs!

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